

**S/N Unknown**

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Leonard Forbes et al.	Examiner:	Ly D. Pham
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	1303.024US2
Title:	INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD		

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**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Patent Application  
Commissioner for Patents  
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Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/945498, filed on August 30, 2001, which is relied upon for an earlier filing date under 35 U.S.C. §120.

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Serial No :Unknown

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Title: INTEGRATED CIRCUIT MEMORY DEVICE AND METHOD

Page 2

Dkt: 1303.024US2

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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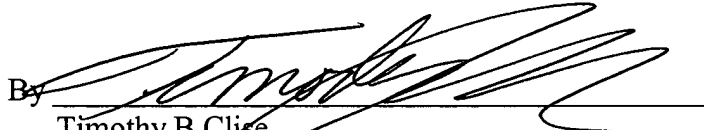
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STATEMENT BY APPLICANT**

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<b>Application Number</b>	Unknown
<b>Filing Date</b>	Even Date Herewith
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	Unknown
<b>Examiner Name</b>	Pham, Ly

Sheet 1 of 5

Attorney Docket No: 1303.024US2

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Substitute Disclosure Statement Form (PTO-1449)

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Pham, Ly
Sheet 2 of 5	Attorney Docket No: 1303.024US2	

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T <sup>2</sup>
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Substitute Disclosure Statement Form (PTO-1449)

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	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Pham, Ly
Sheet 3 of 5	Attorney Docket No: 1303.024US2	

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